

## N-Channel Enhancement Mode Field Effect Transistor

### General Description

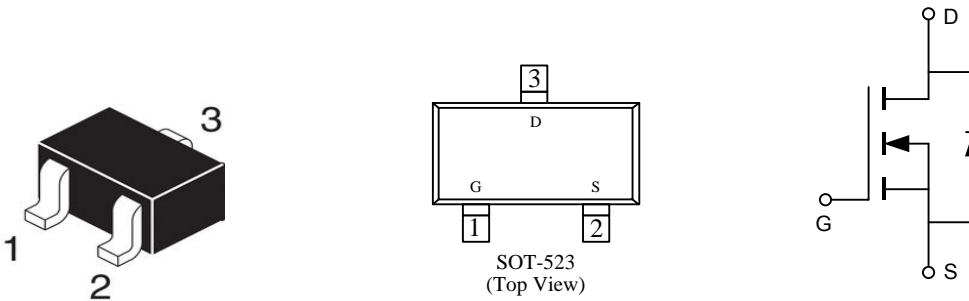
Product Summary		
$V_{DSS}$	$I_D$	$R_{DS(ON)}(m\Omega)TYP$
20V	0.65A	260 @ $V_{GS}= 4.5V$
	0.55A	320 @ $V_{GS}= 2.5V$

### Features

- Super high dense cell design for low  $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-523 package

### Package

- SOT-523



### Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2308B	-55°C to +150°C	SOT-523	3000

### Absolute Maximum Ratings

( $T_A=25^\circ C$  unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	$V_{DSS}$	20	V
Gate-source voltage	$V_{GSS}$	$\pm 12$	V
Coutinuous drain current ( $T_j=150^\circ C$ )	$I_D$	$T_A=25^\circ C$	0.65
		$T_A=80^\circ C$	0.45
Pulsed drain current	$I_{DM}$	2.5	A
Drain-source Diode forward current	$I_S$	0.3	A
Power dissipation	$P_D$	$T_A=25^\circ C$	0.27
		$T_A=70^\circ C$	0.16
Operating junction Temperature range	$T_j$	-55—150	$^\circ C$